NTQD6968N

Power MOSFET

7.0 A, 20 V, Common Drain, Dual N−Channel, TSSOP−8

ON Semiconductor®

http://onsemi.com

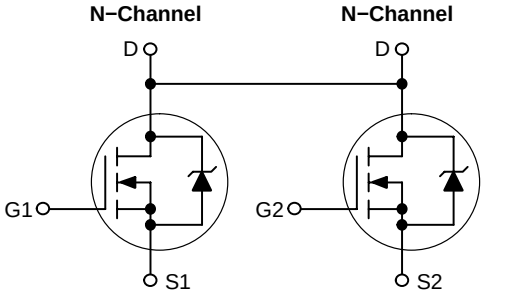
Features

- Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Logic Level Gate Drive
- 3 mm Wide TSSOP−8 Surface Mount Package
- High Speed, Soft Recovery Diode
- TSSOP−8 Mounting Information Provided
- Pb−Free Package is Available

Applications

- Battery Protection Circuits

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
20 V	17 mΩ @ 4.5 V	7.0 A



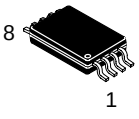
MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage	V_{DSS}	20	Vdc
Gate−to−Source Voltage − Continuous	V_{GS}	±12	Vdc
Drain Current − Continuous @ T_A 25°C (Note 1) − Continuous @ T_A 70°C (Note 1) − Pulsed (Note 3)	 I_D I_D I_{DM}	 7.0 5.6 20	Adc
Total Power Dissipation @ T_A 25°C (Note 1)	P_D	1.81	W
Drain Current − Continuous @ T_A 25°C (Note 2) − Continuous @ T_A 70°C (Note 2) − Pulsed (Note 3)	 I_D I_D I_{DM}	 6.2 4.9 18	Adc
Total Power Dissipation @ T_A 25°C (Note 2)	P_D	1.39	W
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
Thermal Resistance − Junction−to−Ambient (Note 1) Junction−to−Ambient (Note 2)	$R_{\theta JA}$	 69 90	°C/W
Maximum Lead Temperature for Soldering Purposes for 10 seconds	TL	260	°C

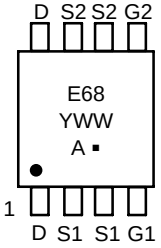
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Mounted onto a 2″ square FR−4 Board (1 in sq, 2 oz. Cu 0.06″ thick single sided), t ≤ 10 sec.
2. Mounted onto a 2″ square FR−4 Board (1 in sq, 2 oz. Cu 0.06″ thick single sided), Steady State.
3. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

MARKING DIAGRAM & PIN ASSIGNMENT



TSSOP−8
CASE 948S
PLASTIC



E68 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NTQD6968N	TSSOP−8	100 Units / Rail
NTQD6968NR2	TSSOP−8	4000/Tape & Reel
NTQD6968NR2G	TSSOP−8 (Pb−Free)	4000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain−to−Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 250 μAdc)	$V_{(BR)DSS}$	20	–	–	Vdc
Temperature Coefficient (Positive)		–	16	–	mV/°C
Zero Gate Voltage Collector Current (V_{DS} = 16 Vdc, V_{GS} = 0 Vdc, T_J = 25°C)	I_{DSS}	–	–	1.0	μAdc
(V_{DS} = 16 Vdc, V_{GS} = 0 Vdc, T_J = 125°C)		–	–	10	
Gate−Body Leakage Current (V_{GS} = ±12 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	–	–	±100	nAdc
ON CHARACTERISTICS					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μAdc)	$V_{GS(th)}$	0.6	0.75	1.2	Vdc
Temperature Coefficient (Negative)		–	3.0	–	mV/°C
Static Drain−to−Source On−State Resistance (V_{GS} = 4.5 Vdc, I_D = 7.0 Adc)	$R_{DS(on)}$	–	0.017	0.022	Ω
(V_{GS} = 2.5 Vdc, I_D = 7.0 Adc)		–	0.022	0.030	
(V_{GS} = 2.5 Vdc, I_D = 3.5 Adc)		–	0.022	0.030	
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 7.0 Adc)	g_{FS}	–	19.2	–	Mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	C_{iss}	–	630	–	pF
Output Capacitance (V_{DS} = 16 Vdc, V_{GS} = 0 Vdc, f = 1.0 MHz)	C_{oss}	–	260	–	
Transfer Capacitance	C_{rss}	–	95	–	
SWITCHING CHARACTERISTICS (Notes 4 and 5)					
Turn−On Delay Time	$t_{d(on)}$	–	8.0	–	ns
Rise Time (V_{DD} = 16 Vdc, I_D = 7.0 Adc, V_{GS} = 4.5 Vdc, R_G = 6.0 Ω)	t_r	–	25	–	
Turn−Off Delay Time	$t_{d(off)}$	–	60	–	
Fall Time	t_f	–	65	–	
Gate Charge (V_{DS} = 16 Vdc, V_{GS} = 4.5 Vdc, I_D = 7.0 Adc)	Q_{tot}	–	12.5	17	nC
	Q_{gs}	–	1.0	–	
	Q_{gd}	–	5.0	–	
BODY−DRAIN DIODE RATINGS (Note 4)					
Forward On−Voltage (I_S = 7.0 Adc, V_{GS} = 0 Vdc)	V_{SD}	–	0.82	1.2	Vdc
Reverse Recovery Time	t_{rr}	–	35	–	ns
(I_S = 7.0 Adc, V_{GS} = 0 Vdc, dI_S/dt = 100 A/μs)	t_a	–	15	–	
	t_b	–	20	–	
Reverse Recovery Stored Charge	Q_{RR}	–	0.02	–	μC

4. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.
5. Switching characteristics are independent of operating junction temperature.

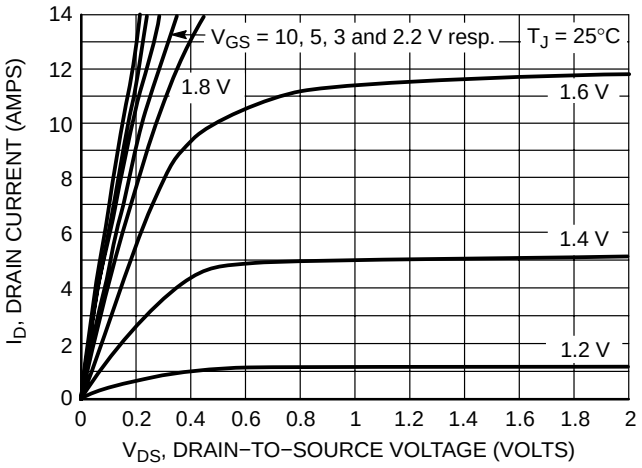


Figure 1. On−Region Characteristics

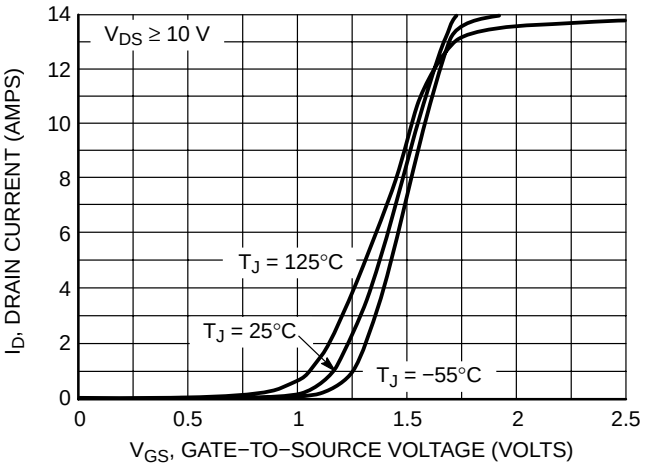


Figure 2. Transfer Characteristics

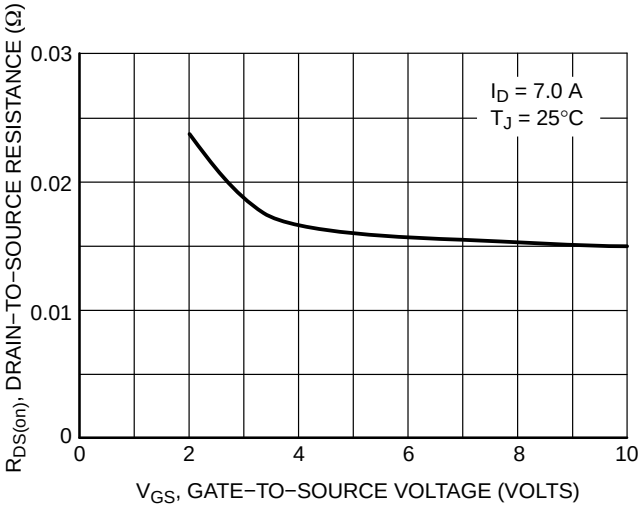


Figure 3. On−Resistance versus Gate−to−Source Voltage

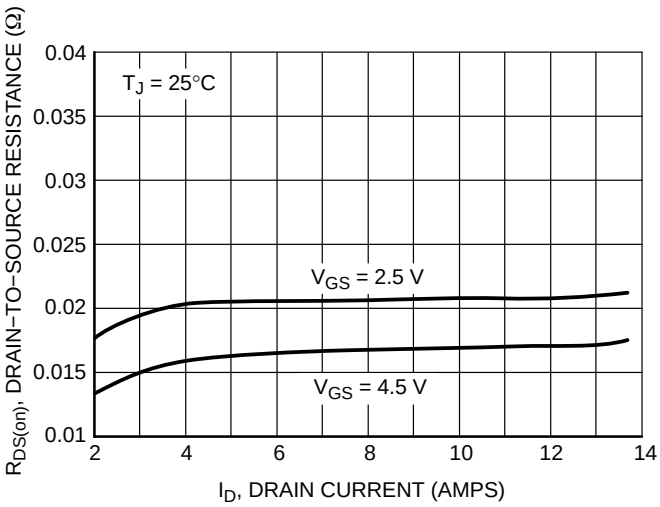


Figure 4. On−Resistance versus Drain Current and Gate Voltage

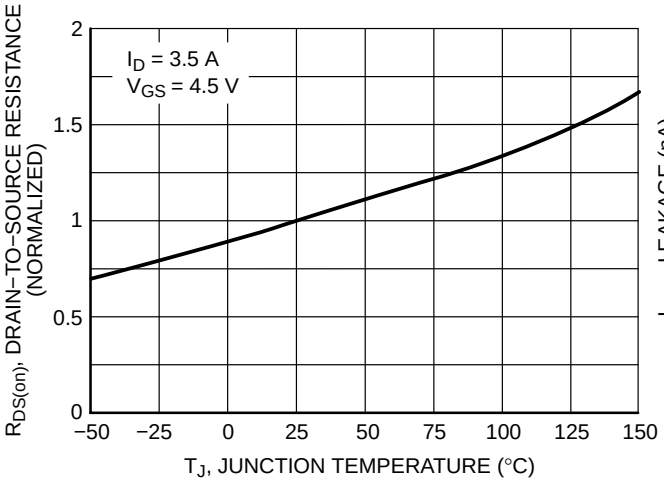


Figure 5. On−Resistance Variation with Temperature

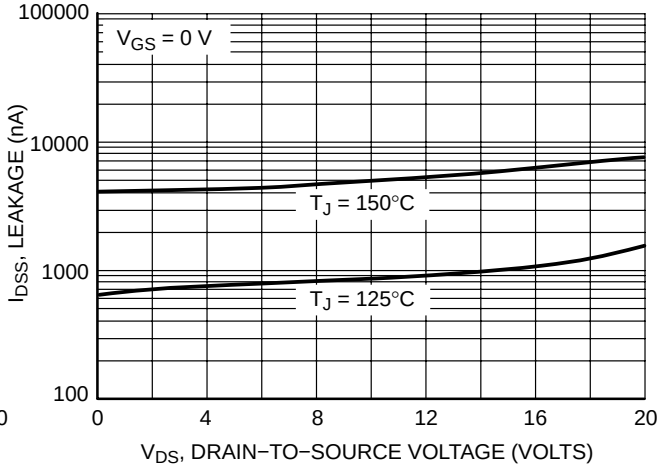


Figure 6. Drain−to−Source Leakage Current versus Voltage

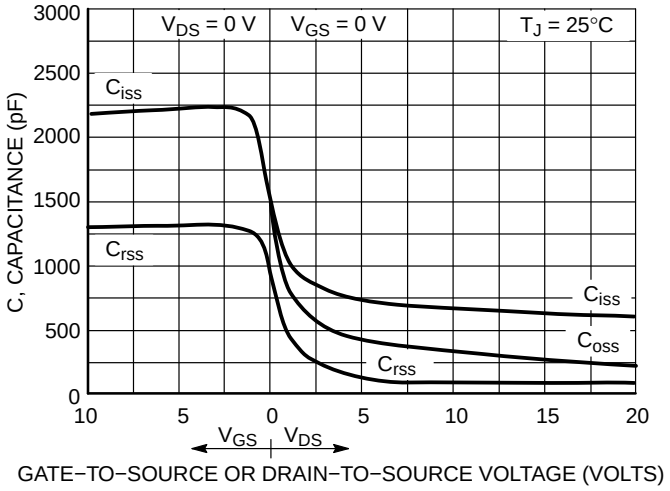


Figure 7. Capacitance Variation

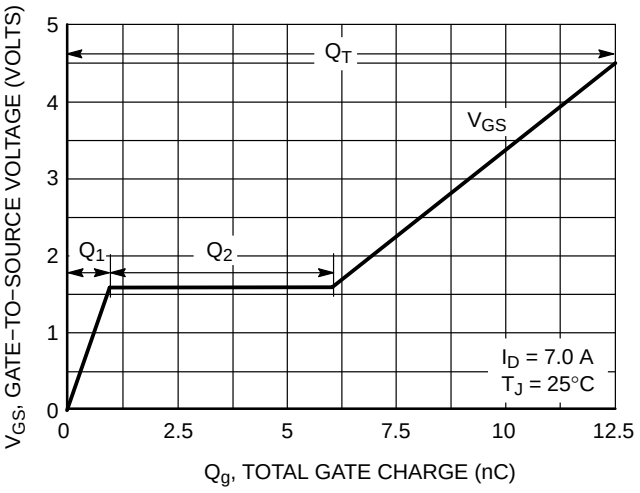


Figure 8. Gate−to−Source Voltage versus Total Charge

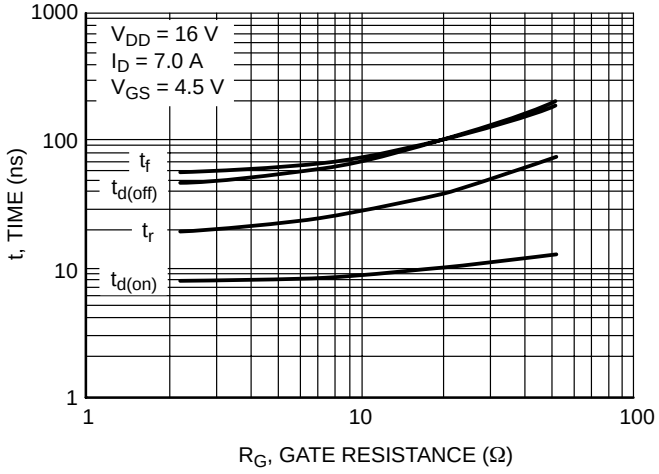


Figure 9. Resistive Switching Time Variation versus Gate Resistance

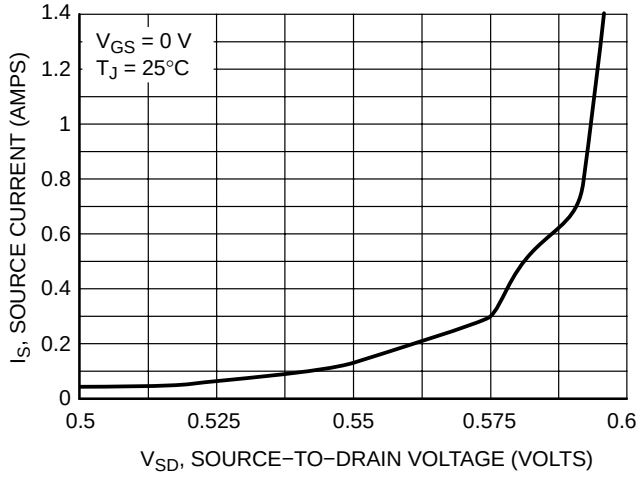


Figure 10. Diode Forward Voltage versus Current

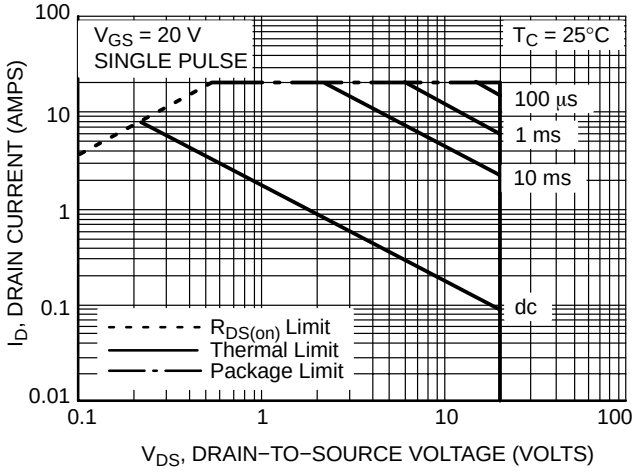


Figure 11. Maximum Rated Forward Biased Safe Operating Area

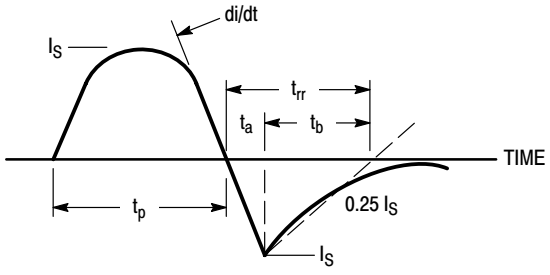


Figure 12. Diode Reverse Recovery Waveform

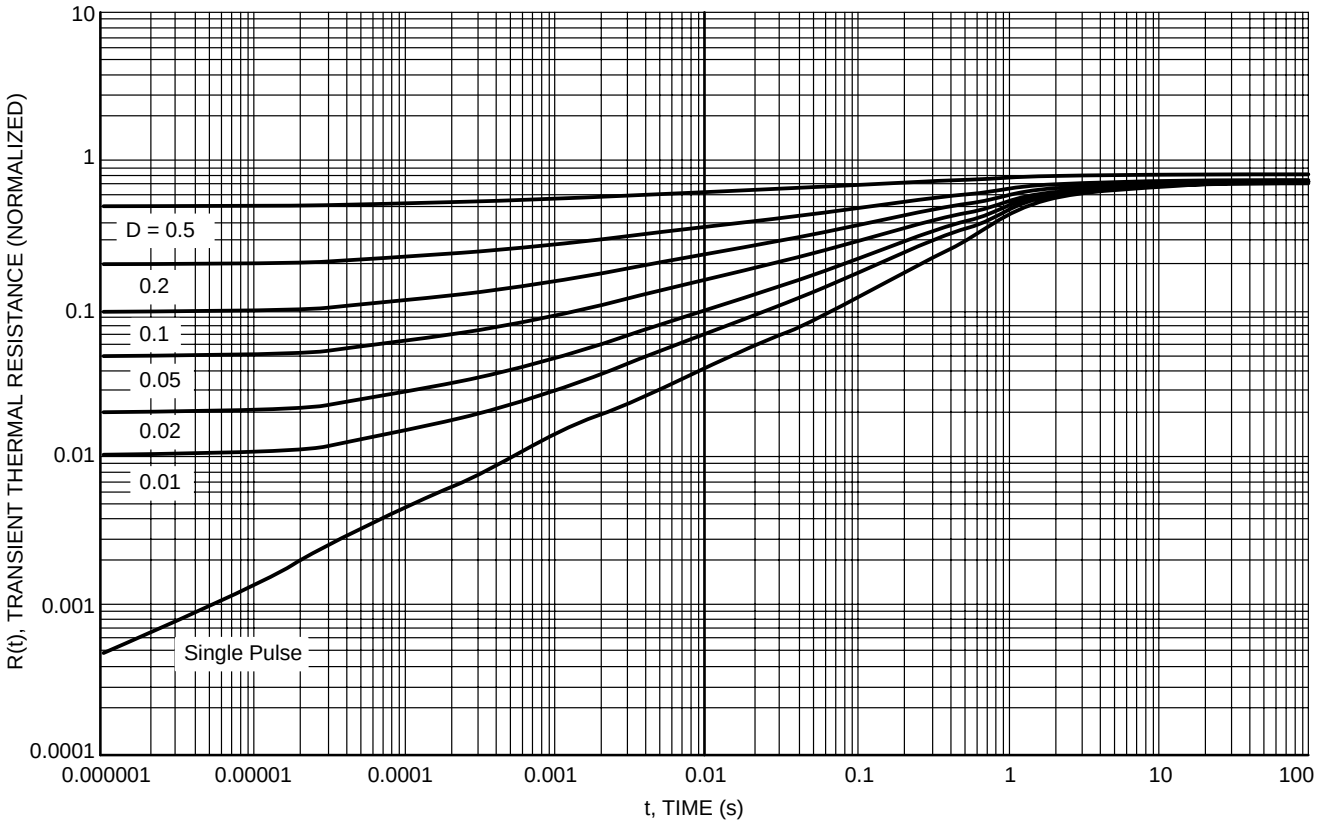
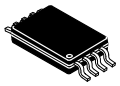


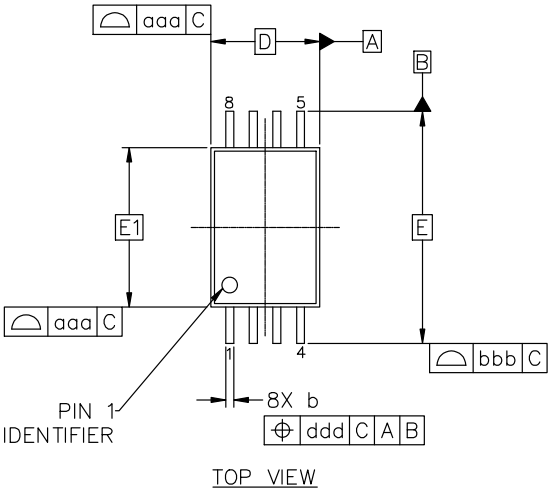
Figure 13. Thermal Response



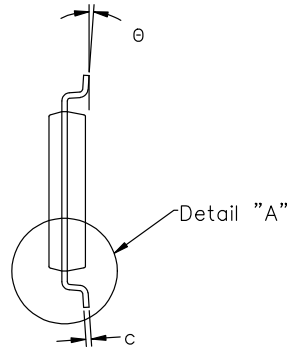
SCALE 2:1

TSSOP−8 3.00x4.00x0.90, 0.65P
CASE 948S
ISSUE D

DATE 24 OCT 2025

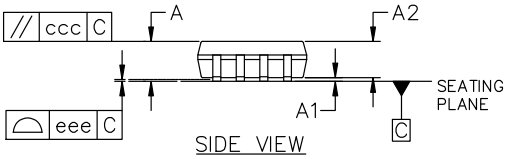


TOP VIEW

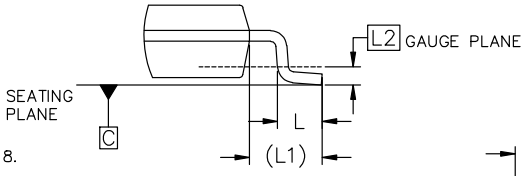


FRONT VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.05	0.10	0.15
A2	0.80	0.90	1.00
b	0.19	0.25	0.30
c	0.09	0.15	0.20
D	3.00 BSC		
E	6.40 BSC		
E1	4.40 BSC		
L	0.50	0.60	0.70
L1	1.00 REF		
L2	0.25 BSC		
θ	0°	4°	8°
TOLERANCE FORM & POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.10		
eee	0.05		

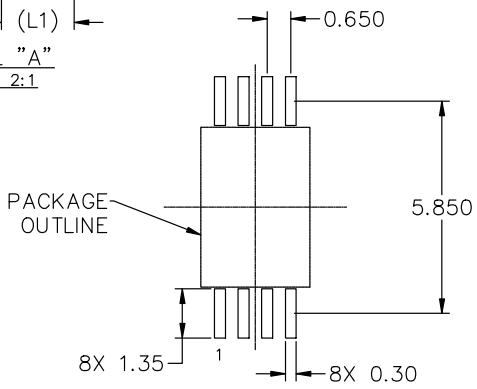


SIDE VIEW



DETAIL "A"
SCALE 2:1

NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION "D" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSION OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.
4. DIMENSION "E1" DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 PER SIDE.
5. DIMENSION "b" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08mm TOTAL IN EXCESS OF THE "b" DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD IS 0.07mm.



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TSSOP−8 3.00x4.00x0.90, 0.65P**	**PAGE 1 OF 1**

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